

IRL3202PbF

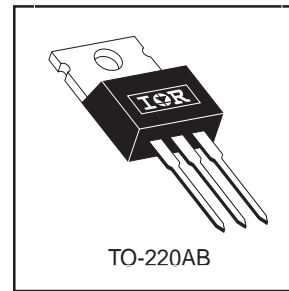
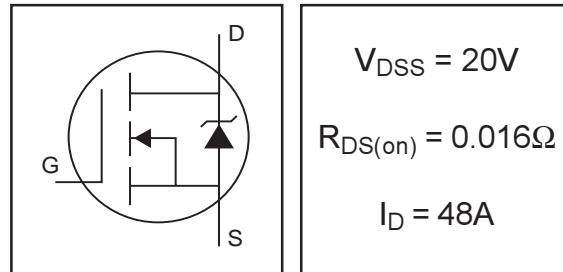
HEXFET® Power MOSFET

- Advanced Process Technology
- Optimized for 4.5V-7.0V Gate Drive
- Ideal for CPU Core DC-DC Converters
- Fast Switching
- Lead-Free

Description

These HEXFET Power MOSFETs were designed specifically to meet the demands of CPU core DC-DC converters in the PC environment. Advanced processing techniques combined with an optimized gate oxide design results in a die sized specifically to offer maximum efficiency at minimum cost.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



Absolute Maximum Ratings

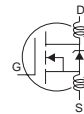
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	48	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	30	
I_{DM}	Pulsed Drain Current $\text{\textcircled{D}}$	190	
$P_D @ T_C = 25^\circ C$	Power Dissipation	69	W
	Linear Derating Factor	0.56	W/°C
V_{GS}	Gate-to-Source Voltage	± 10	V
V_{GSM}	Gate-to-Source Voltage (Start Up Transient, $t_p = 100\mu s$)	14	V
E_{AS}	Single Pulse Avalanche Energy $\text{\textcircled{A}}$	270	mJ
I_{AR}	Avalanche Current $\text{\textcircled{A}}$	29	A
E_{AR}	Repetitive Avalanche Energy $\text{\textcircled{A}}$	6.9	mJ
dv/dt	Peak Diode Recovery dv/dt $\text{\textcircled{D}}$	5.0	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	1.8	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	---	
$R_{\theta JA}$	Junction-to-Ambient	---	62	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	20	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.019	Ω	V _{GS} = 4.5V, I _D = 29A ④
		—	—	0.016		V _{GS} = 7.0V, I _D = 29A ④
V _{GS(th)}	Gate Threshold Voltage	0.70	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	28	—	—	S	V _{DS} = 16V, I _D = 29A
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 20V, V _{GS} = 0V
		—	—	250		V _{DS} = 10V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 10V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -10V
Q _g	Total Gate Charge	—	—	43	nC	I _D = 29A
Q _{gs}	Gate-to-Source Charge	—	—	12		V _{DS} = 16V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	13		V _{GS} = 4.5V, See Fig. 6 ④
t _{d(on)}	Turn-On Delay Time	—	9.8	—	ns	V _{DD} = 10V
t _r	Rise Time	—	100	—		I _D = 29A
t _{d(off)}	Turn-Off Delay Time	—	63	—		R _G = 9.5Ω, V _{GS} = 4.5V
t _f	Fall Time	—	82	—		R _D = 0.3Ω, ④
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	2000	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	800	—		V _{DS} = 15V
C _{rss}	Reverse Transfer Capacitance	—	290	—		f = 1.0MHz, See Fig. 5



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	48	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	190		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 29A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	68	100	ns	T _J = 25°C, I _F = 29A
Q _{rr}	Reverse Recovery Charge	—	130	190	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting T_J = 25°C, L = 0.64mH
R_G = 25Ω, I_{AS} = 29A.
- ③ I_{SD} ≤ 29A, di/dt ≤ 63A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

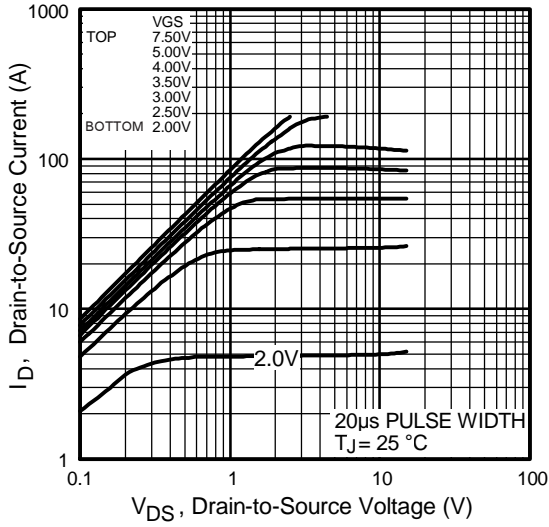


Fig 1. Typical Output Characteristics

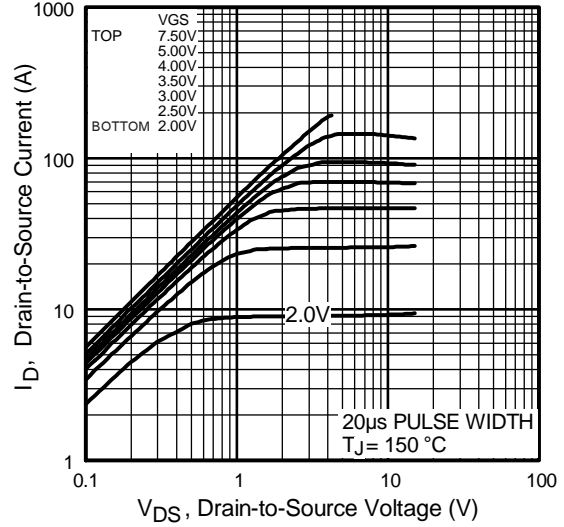


Fig 2. Typical Output Characteristics

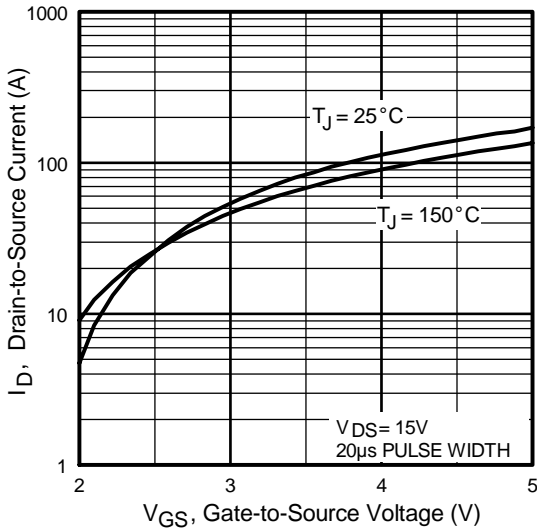


Fig 3. Typical Transfer Characteristics

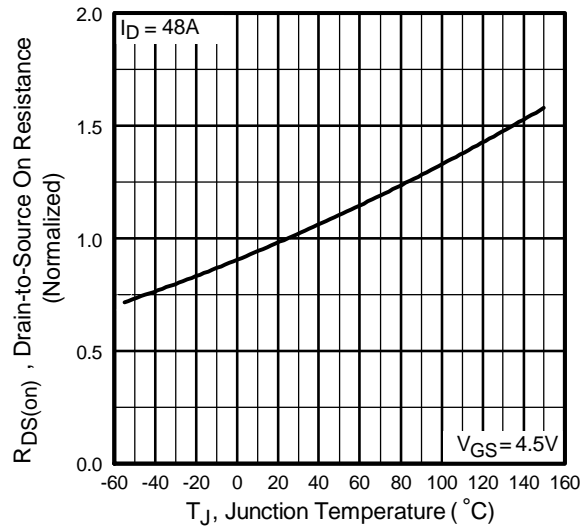


Fig 4. Normalized On-Resistance Vs. Temperature

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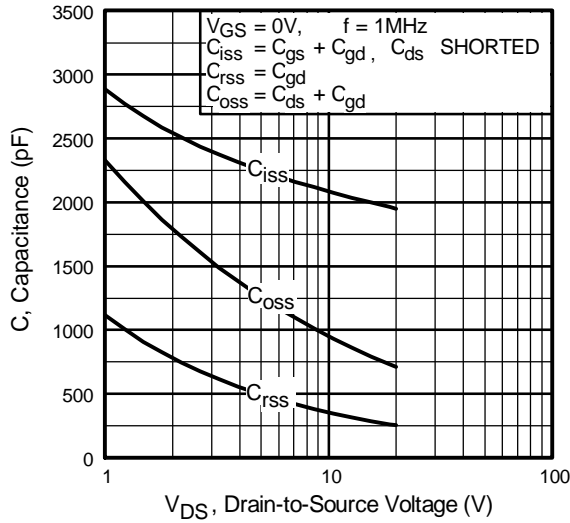


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

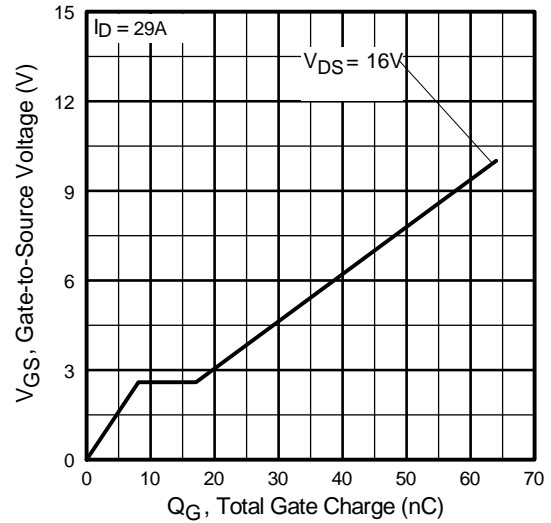


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

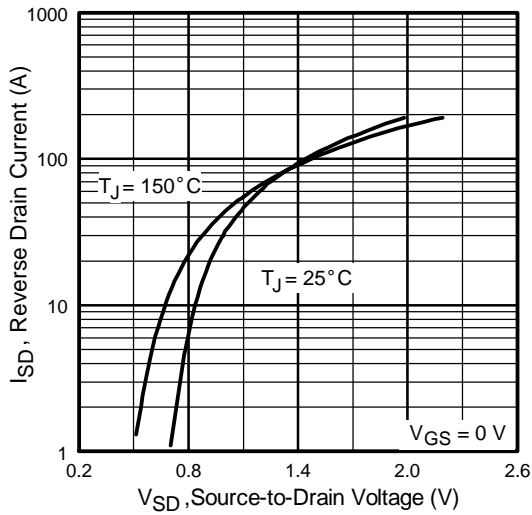


Fig 7. Typical Source-Drain Diode Forward Voltage

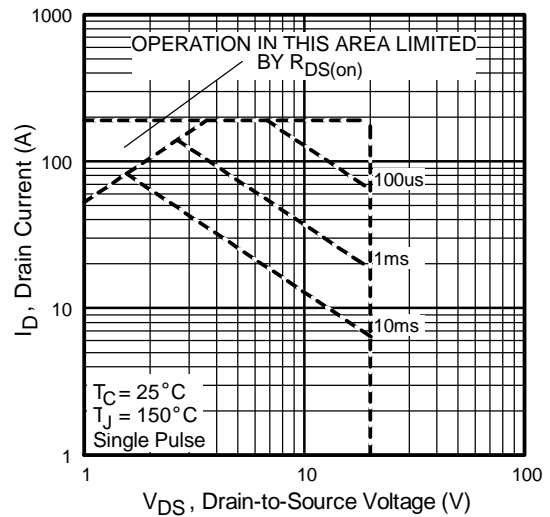


Fig 8. Maximum Safe Operating Area

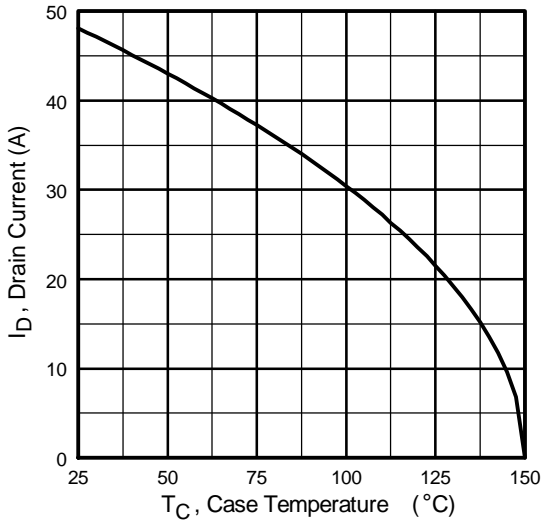


Fig 9. Maximum Drain Current Vs. Case Temperature

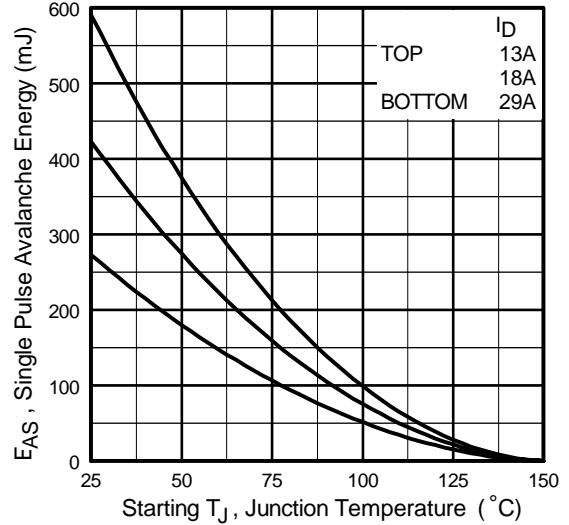


Fig 10. Maximum Avalanche Energy Vs. Drain Current

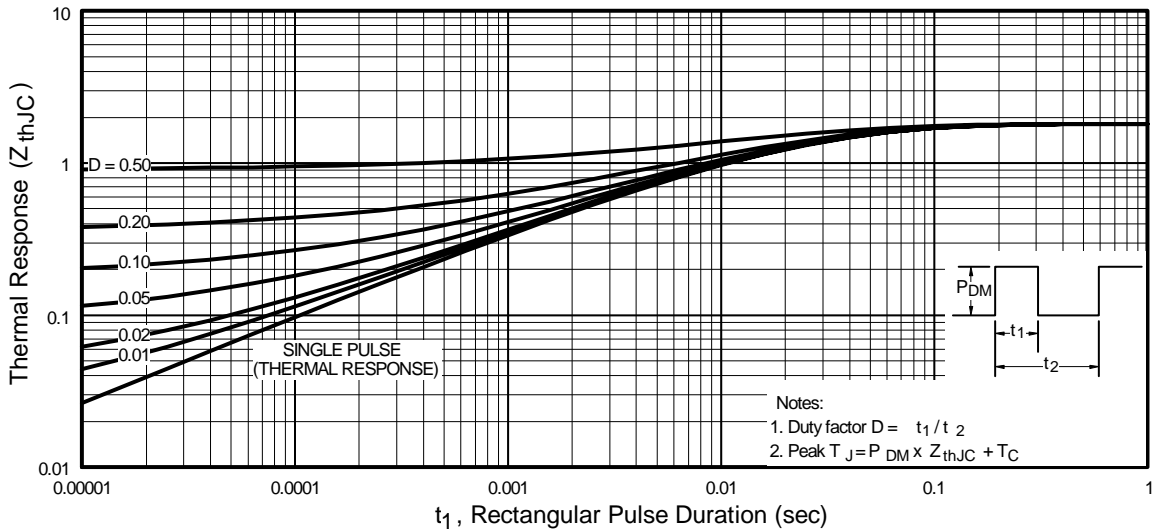


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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International
IR Rectifier

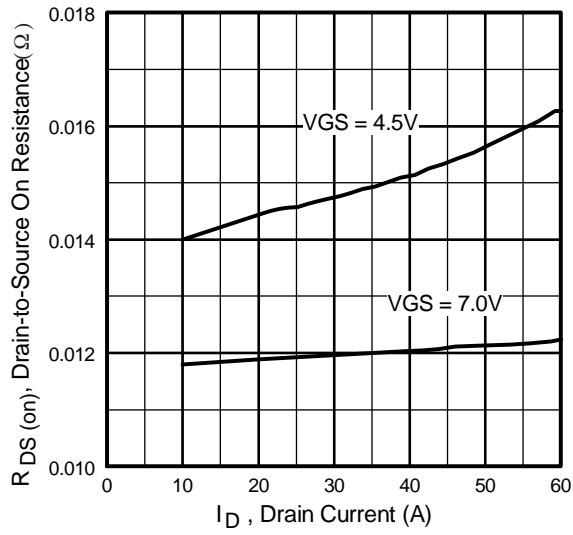


Fig 12. On-Resistance Vs. Drain Current

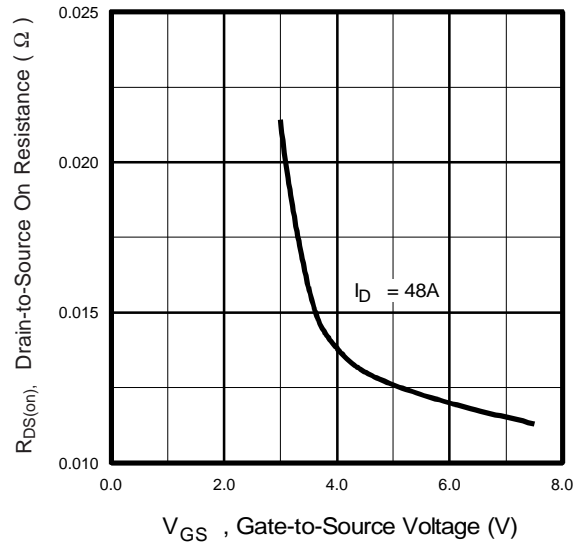
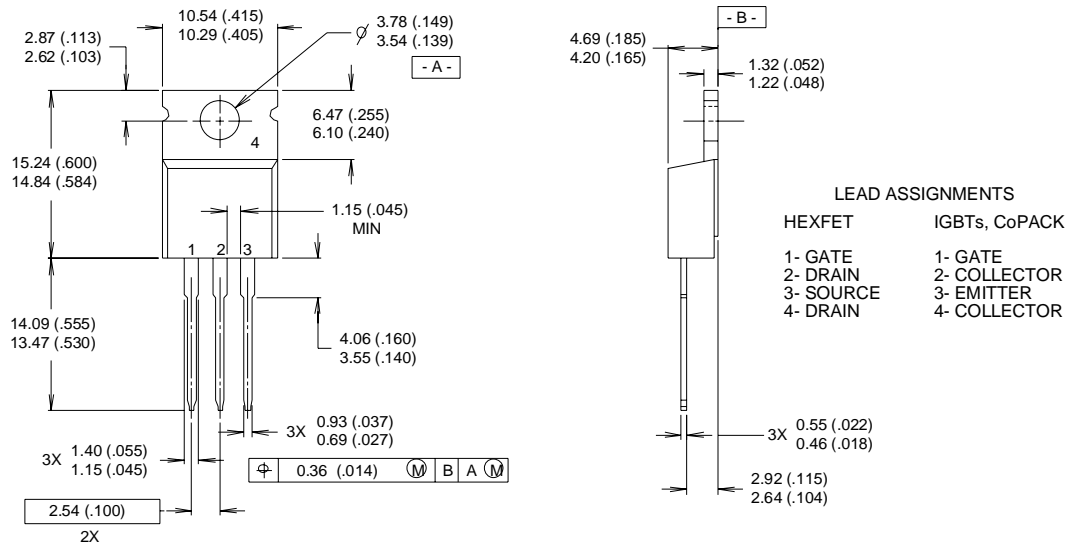


Fig 13. On-Resistance Vs. Gate Voltage

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

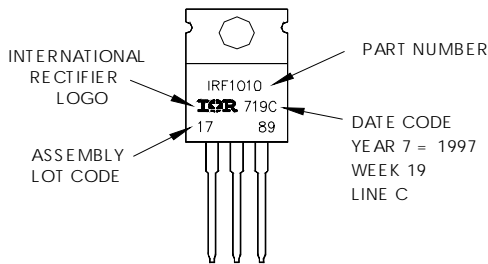


NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH
- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line
 position indicates "Lead-Free"



Data and specifications subject to change without notice.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>